SAMYANG ELECTRONICS

KBU8005 --- KBU810

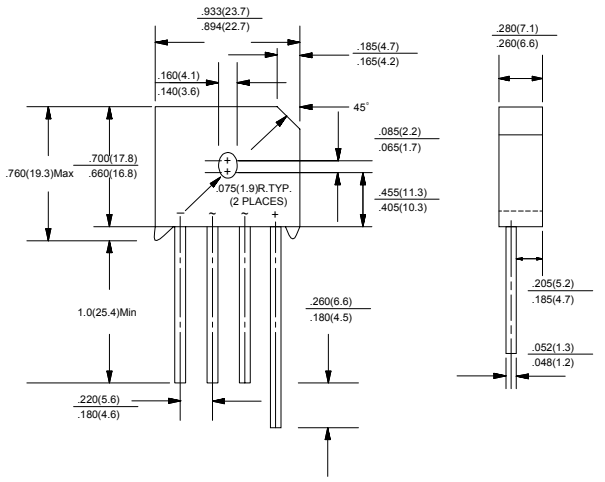
SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V
CURRENT: 8.0A

FEATURES

- ◇ Rating to 1000V PRV
- ◇ Surge overload rating to 250 Amperes peak
- ◇ Ideal for printed circuit board
- ◇ Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- ◇ Lead solderable per MIL-STD-202 method 208

KBU



Dimensions in inches and (mm)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		KBU 8005	KBU 801	KBU 802	KBU 804	KBU 806	KBU 808	KBU 810	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forw ard output current @T_A=50℃	$I_{F(AV)}$	8.0							A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load	I_{FSM}	250.0							A
Maximum instantaneous forw ard voltage @ 4.0 A	V_F	1.0							V
Maximum reverse current @T_A=25℃	I_R	10.0							μA
at rated DC blocking voltage @T_A=100℃		1.0							mA
Operating junction temperature range	T_J	- 55 ---- + 125							℃
Storage temperature range	T_{STG}	- 55 ---- + 150							℃

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FIG.1 – TYPICAL FORWARD CURRENT DERATING CURVE

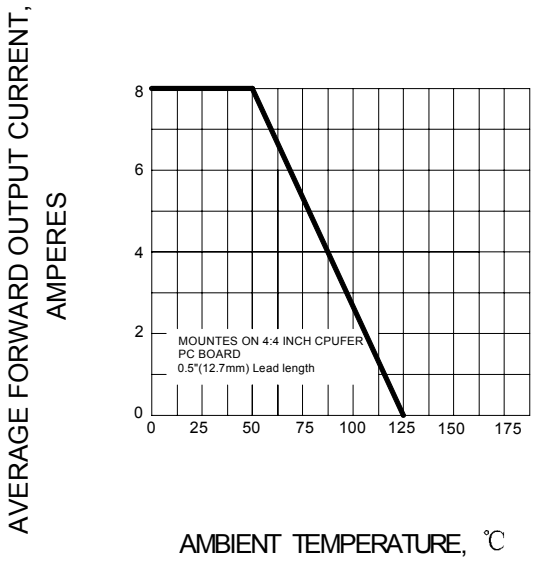


FIG.2 – MAXIMUM FORWARD SURGE CURRENT

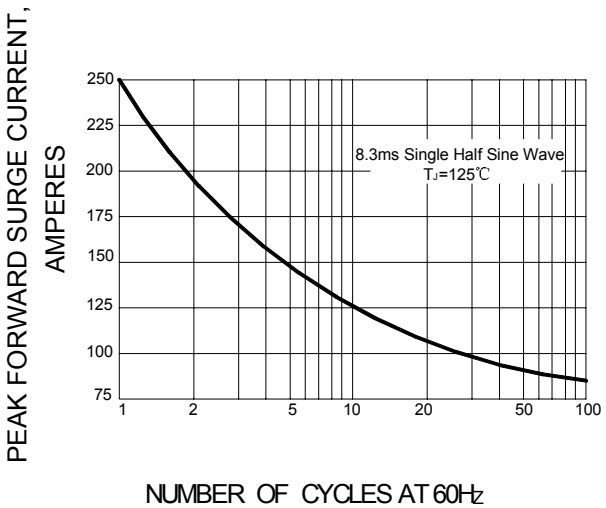


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

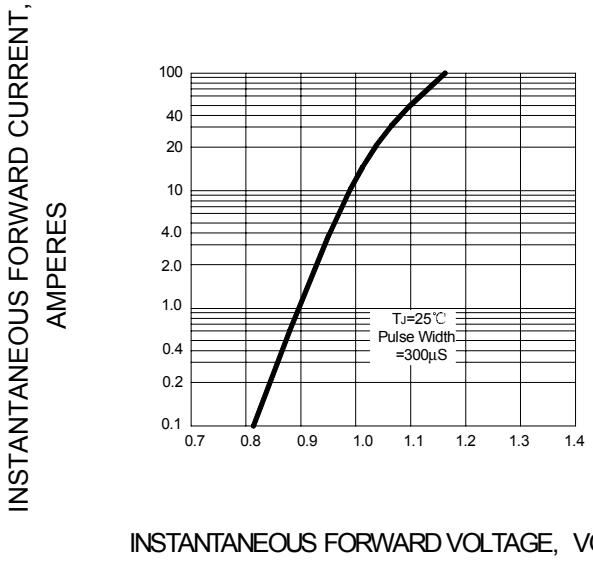


FIG.4 – TYPICAL REVERSE CHARACTERISTIC

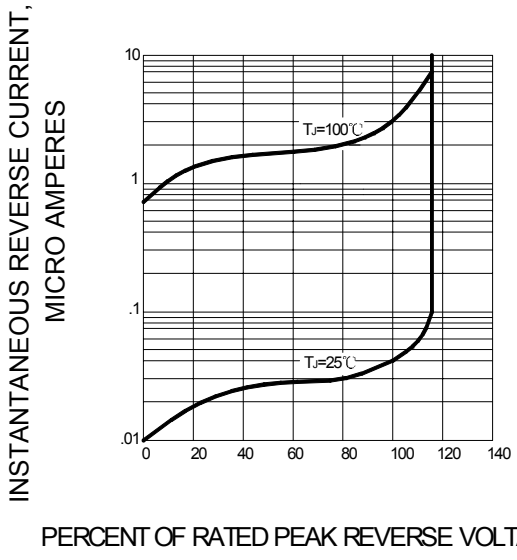


FIG.5 – TYPICAL JUNCTION CAPACITANCE PER ELEMENT

